

Amendments to the Claims

This listing of the Claims will replace all prior versions and listings of the claims in this patent application.

Listing of the Claims

1-14. (canceled)

15. (New) A method for fabricating a semiconductor wafer with a contact point comprising gold, comprising:

cleaning said contact point; and

after said cleaning said contact point, testing said semiconductor wafer by using a testing element contacting said contact point.

16. (New) The method of claim 15, wherein said contact point is provided by a circuit pad.

17. (New) The method of claim 15, wherein said cleaning said contact point comprises ion milling with argon.

18. (New) The method of claim 15, wherein said cleaning said contact point comprises ion milling with helium.

19. (New) The method of claim 15, wherein said cleaning said contact point comprises ion milling with neon.

20. (New) The method of claim 15, wherein said testing element comprises a probe contacting said contact point.

21. (New) A method for fabricating a semiconductor wafer comprising a passivation layer and a pad, an opening in said passivation layer exposing said pad, comprising:

cleaning said pad; and

after said cleaning said pad, testing said semiconductor wafer by using a testing element contacting said pad.

22. (New) The method of claim 21, wherein said pad comprises aluminum.

23. (New) The method of claim 21, wherein said cleaning said pad comprises ion milling with argon.

24. (New) The method of claim 21, wherein said cleaning said pad comprises ion milling with helium.

25. (New) The method of claim 21, wherein said cleaning said pad comprises ion milling with neon.

26. (New) The method of claim 21, wherein said testing element comprises a probe contacting said contact point.

27. (New) A method for fabricating a semiconductor wafer, comprising:

depositing a bump on a topmost patterned circuit layer of said semiconductor wafer, wherein said bump comprises a pillar-shaped portion;

cleaning said bump; and

after said cleaning said bump, testing said semiconductor wafer by using a testing element contacting said bump.

28. (New) The method of claim 27, wherein a top surface of said bump is substantially flat.

29. (New) The method of claim 27, wherein said bump has a top surface and a side surface, wherein said top and side surfaces are connected with discontinuity.

30. (New) The method of claim 27, wherein said cleaning said bump comprises ion milling with argon.

31. (New) The method of claim 27, wherein said cleaning said bump comprises ion milling with helium.

32. (New) The method of claim 27, wherein said cleaning said bump comprises ion milling with neon.

33. (New) The method of claim 27, wherein said testing element comprises a probe contacting said contact point.